

I. Number	Hits	Search Text	DB	Time stamp
1	994	gate same (work adj function)	USPAT	2002/07/31 14:59
2	781	(gate same (work adj function)) and transistor	USPAT	2002/07/31 14:56
3	717	((gate same (work adj function)) and transistor) and (thickness thick)	USPAT	2002/07/31 14:57
4	698	((gate same (work adj function)) and transistor) and (thickness thick) and (conduct\$3 metal\$3)	USPAT	2002/07/31 14:57
5	1626	gate same (work adj function)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 15 03
6	1135	(gate same (work adj function)) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 15 00
7	872	((gate same (work adj function)) and transistor) and (thickness thick)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 15 02
8	832	((gate same (work adj function)) and transistor) and (thickness thick) and (conduct\$4 metal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 15 03
9	832	((gate same (work adj function)) and transistor) and (thickness thick) and (conduct\$4 metal\$4) and (work adj function)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 16 37
10	600	(work adj function).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 15:04
11	21	((gate same (work adj function)) and transistor) and (thickness thick) and (conduct\$4 metal\$4) and (work adj function) and (work adj function).ti.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 15 04
12	1		USPAT	2002/07/31 15 33
13	1		USPAT	2002/07/31 15 35
14	1		USPAT	2002/07/31 15 47
15	1		USPAT	2002/07/31 15 55
16	1	((work adj function).ti.) and critical adj thickness\$3	USPAT	2002/07/31 16 38
17	50	((work adj function).ti.) and (first second)	USPAT	2002/07/31 17:04
18	1		USPAT	2002/07/31 16 43
19	1		USPAT	2002/07/31 16 49
20	0	"6051865".PN. and ((layer material) with work adj function)	USPAT	2002/07/31 17 05
21	0	"6051865".PN. and ((layer material) with (work adj function))	USPAT	2002/07/31 17 06
22	416	((gate same (work adj function)) and transistor) and (thickness thick) and (conduct\$4 metal\$4) and (work adj function) and ((layer material) with (work adj function))	USPAT	2002/07/31 17 08
23	92	((gate same (work adj function)) and transistor) and (thickness thick) and (conduct\$4 metal\$4) and (work adj function) and ((layer material) with (work adj function)) and ((first second) with (work adj function))	USPAT	2002/07/31 17 09
24	489	((gate same (work adj function)) and transistor) and (thickness thick) and (conduct\$4 metal\$4) and (work adj function) and ((layer material) with (work adj function))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 17 08

117 ((((((gate same (work adj function)) and transistor) and (thickness thick))  
and (conduct\$4 metal\$4)) and (work adj function)) and ((layer material)  
with (work adj function))) and ((first second) with (work adj function))

USPAT:  
US-PGPUB;  
EPO; JPO;  
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